Determining the current polarization in Al/Co nanostructured point contacts

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We present a study of the Andreev reflections in superconductor/ferromagnet nanostructured point contacts. The experimental data are analyzed in the frame of a model with two spin-dependent transmission coefficients for the majority and minority charge carriers in the ferromagnet. This model consistently describes the whole set of conductance measurements as a function of voltage, temperature, and magnetic field. The ensemble of our results shows that the degree of spin polarization of the current can be unambiguously determined using Andreev physics.

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The field of spintronics is largely based on the ability of ferromagnetic materials to conduct spin-polarized currents. 1 Thus, the experimental determination of the degree of current polarization has become a key issue. Recently the analysis of Andreev reflections in superconductor/ferromagnet (S/F) point contacts has been used to extract this spin polarization in a great variety of materials. 2–7 The underlying idea is the sensitivity of the Andreev process to the spin of the carriers, which in a spin-polarized situation is manifested in a reduction of its probability. 8 The theoretical analysis of these S/F point-contact experiments has been mainly carried out following the ideas of the Blonder-Tinkham-Klapwijk (BTK) theory. 9 Different generalizations of this model to spin-polarized systems have been proposed, in which an additional phenomenological parameter $P$, the spin polarization of the ferromagnet, excellent fits to the experimental data have been obtained. 2–7 However, a microscopic justification of these models is lacking. 10–12 Recently, Xia et al. 13 have combined ab initio methods with the scattering formalism to analyze the Andreev reflection in spin-polarized systems. Their main conclusion is that, in spite of the success in fitting the experiments, these modified BTK models do not correctly describe the transport through S/F interfaces. Therefore, at this stage several basic questions arise: what is the minimal model that describes on a microscopic footing the Andreev reflection in spin-polarized systems? More importantly, can the current polarization be experimentally determined using Andreev physics?

In this Rapid Communication we address these questions both experimentally and theoretically. We present measurements of the differential resistance of nanostructured Al/Co point contacts as a function of voltage, temperature, and magnetic field. To analyze the experimental data we have developed a model based on quasiclassical Green functions, the main ingredients of which are two transmission coefficients accounting for the majority- and minority-spin bands in the ferromagnet. We show that this model consistently describes the whole set of data, which unambiguously demonstrates that the spin polarization of current in a ferromagnet can indeed be determined employing Andreev reflection.

We have fabricated Al/Co point contacts following the process described in Ref. 14. Briefly, a bowl-shaped hole is drilled through a 50 nm thick silicon nitride (Si$_{3+x}$N$_{4-x}$) membrane by means of electron-beam lithography and reactive ion etching. The smallest opening in the insulating membrane has typically a diameter of 5 nm. Finally, 200 nm of Al and $d_{Co} = 6, 12, 24, 50$ nm of Co plus $200$ nm $- d_{Co}$ of Cu are deposited by electron-beam evaporation under ultrahigh vacuum conditions ($\sim 10^{-9}$ mbar) on each side of the membrane. A schematic of the samples is shown in Fig. 1(a). The differential resistance $R$ was measured with lock-in technique in a dilution refrigerator. A dc current was superimposed on the small measuring ac component and both $R$ and the voltage drop $V$ were recorded simultaneously.

As a reference we show in Fig. 1(b) the Andreev spectrum, i.e., the differential conductance $G$ as a function of the voltage $V$ of an Al/Cu sample. In all the spectra in this paper, $G$ and $V$ have been normalized by the normal-state conductance $G_N$ and by the zero-temperature superconducting gap $\Delta$ of the Al electrode, respectively. $G_N$ showed to be completely independent of $V$ in the range $eV \leq (5-10)\Delta$. Since the estimated mean free paths of the Cu and Al electrodes are $\sim 60$ nm or longer at low temperatures, all the contacts studied are in the ballistic regime. In the Al/Cu case [Fig. 1(b)] the BTK theory fits the experimental data very well (see figure caption for details). In the case of Al/Co, the ferromagnetic layer causes a reduction of the Andreev spectrum amplitude as compared to the Al/Cu contacts (see Fig. 2).

**FIG. 1.** (Color online) (a) Schematic of an Al/Co nanocontact. (b) Andreev spectrum of an Al/Cu contact at 95 mK (black circles). The dashed line is the fit obtained with the BTK theory (Ref. 9) yielding the transmission $\tau = 0.781$ and the gap $\Delta = 206$ $\mu$eV.
reduces to the BTK result. The normal-state conductance is given by
\[ G_N = \frac{4e^2}{h} \left( \frac{\tau_1 \tau_2}{(1 + r_1 r_2)^2} - 4r_1 r_2 (eV/\Delta)^2 \right), \]
for \( eV \ll \Delta \), and
\[ G_N = \frac{4e^2}{h} \left( \frac{\tau_1 \tau_2}{(1 - r_1 r_2) + (1 + r_1 r_2) \sqrt{1 - (\Delta/eV)^2}} \right)^2, \]
for \( eV \gg \Delta \).

In the absence of spin polarization (\( \sigma = \tau_1 \tau_2 \)), this formula reduces to the BTK result. The normal-state conductance is given by
\[ G_N = \frac{4e^2}{h} \left( \frac{\tau_1}{\tau_1 + \tau_2} \right)^2, \]
and the current polarization is defined by \( P = |\tau_1 - \tau_2|/(\tau_1 + \tau_2) \). The main approximation of this model is the assumption that we can describe the point contact with a single pair of transmission coefficients \( \tau_{1,1} \), which will be finally justified by the agreement with the experiment.

As we show in Fig. 2, using \( \tau_{1,1} \) and \( \Delta \) as free parameters our model yields an excellent fit to the Andreev spectra of the Al/Co contacts for temperatures \( T \approx 100 \text{ mK} \). These parameters for a total of eight contacts are listed in Table I.

The current \( I_{SF} \) through the S/F point contact is computed following standard procedures. It can be separated in two spin contributions, \( I_{SF} = I_1 + I_1' \), where each can be written in the BTK form
\[ I_\sigma = \frac{e}{h} \int_{-\infty}^{\infty} d\epsilon \left[ n_F(\epsilon - eV) - n_F(\epsilon) \right] \left[ 1 + A_{\sigma'}(\epsilon) - B_{\sigma}(\epsilon) \right] \]
for \( \epsilon < \mu \), where \( n_F \) is the Fermi function, and \( A_{\sigma'}(\epsilon) \) and \( B_{\sigma}(\epsilon) \) are the spin-dependent Andreev reflection and normal reflection probabilities, respectively. These are given by
\[ A_{\sigma} = \tau_{\sigma} s_{\sigma} f(D)^2 \]
and \( B_{\sigma} = (r_{\sigma} + r_{-\sigma}) + (r_{\sigma} - r_{-\sigma}) g(D)^2 \),
where \( s_{\sigma} = \sqrt{1 - \tau_{\sigma}} \) and \( D = (1 + r_{-\sigma} r_{-\sigma}) + (1 - r_{\sigma} r_{-\sigma}) g \). The Green functions are evaluated right at the interface at the superconducting side. In the point-contact geometry we can ignore the proximity effect, which means that \( g = -i e/\sqrt{\Delta^2 - \epsilon^2} \) and \( f = i (\Delta/eV) g \), and the zero-temperature conductance adopts the form
\[ G_{SF} = \frac{4e^2}{h} \left( \frac{\tau_1 \tau_2}{(1 + r_1 r_2)^2} - 4r_1 r_2 (eV/\Delta)^2 \right)^2 \]
along with
\[ G_{SF} = \frac{4e^2}{h} \left( \frac{\tau_1 \tau_2}{(1 - r_1 r_2) + (1 + r_1 r_2) \sqrt{1 - (\Delta/eV)^2}} \right)^2 \]
for \( eV \ll \Delta \), and
\[ G_{SF} = \frac{4e^2}{h} \left( \frac{\tau_1 \tau_2}{(1 - r_1 r_2) + (1 + r_1 r_2) \sqrt{1 - (\Delta/eV)^2}} \right)^2 \]
for \( eV \gg \Delta \).

Their deviations from sample to sample are remarkably small, leading to small uncertainties in the mean values given by \( \tau_1 = 0.40 \pm 0.02 \) and \( \Delta = 190 \pm 10 \) \( \mu \text{eV} \). The total current is of course symmetric with respect to the exchange of \( \tau_1 \) and \( \tau_2 \), which implies that we cannot assign a transmission coefficient to the majority or minority charge carriers in Co. Nevertheless, we expect the high transmissive coefficient \( \tau_1 \) to correspond to the minority electrons, because of their higher density of states at the Fermi level corresponding to the Co 3d band. In our contacts the mean value of the current polarization is \( \bar{P} = 0.42 \pm 0.02 \). An analysis of our experimental data for \( T \)
more stringent test of our model is shown in Fig. 3 simply using the BCS temperature dependence of the gap. As can be seen, the model describes the whole temperature range by the Andreev spectrum of sample No. 2 is depicted. As can be obtained from the spectra at T≈100 mK with our model. The curves are shifted downwards successively by 0.12 units. The red lines are the calculations using the temperature dependence of the zero-bias conductance as a function of the field. The critical field of the Al/Co samples as determined by a fit of the Andreev spectra for sample no. 3 in Fig. 3(b), which illustrates the accuracy in the determination of {τ₁, τ₁}.

We have also measured how a magnetic field H parallel to the insulating layer modifies the Andreev spectra [see Fig. 3(c)]. There are three main effects: (i) the height of the two maxima diminishes with increasing field and their positions are shifted to lower voltages; (ii) as can be seen in the inset of Fig. 3(c), the zero-bias conductance is constant for fields below the critical field; (iii) the transition to the normal state is abrupt. To understand these features we now study how the order parameter Δ is modified by the field. We use two approximations: (a) in the Al electrode the mean free path (l~60 nm) is much smaller than the superconducting coherence length (ξ₀~300 nm), which justifies the use of the diffusive approximation (l<<ξ₀) and the Usadel theory; (b) for our Al films ξ₀ is greater than the electrode thickness d, which means that we can assume that Δ and the Green functions are constant throughout the sample.

With these approximations the Usadel equation reduces to the generic equation that describes the effect of different pair-breaking mechanisms such as magnetic impurities, supercurrents or magnetic fields:

\[ e + iΓg(ε,H) = iΔg(ε,H) \frac{f(ε,H)}{f(ε,H)}, \]

where

\[ \mu_0H_c = 15.0 \text{ mT}. \]
where $D$ is the diffusion constant, $\Gamma$ is a depairing energy, which contains the effect of the magnetic field, and $\langle \hat{A}^2 \rangle$ is the average value of the square of the vector potential along the thickness of the Al film. Additionally, the order parameter $\Delta$ must be determined self-consistently. In Al the London penetration depth is typically $\lambda_0 \sim 50$ nm, which in our case is smaller than the thickness $d$. This implies that the external field is partially screened inside the sample. Thus, the vector potential appearing in Eq. (4) must be determined solving the Maxwell equation \( \nabla^2 \hat{A} = -(4 \pi/c) \hat{j} \), where $\hat{j}$ is the supercurrent density given by $\hat{j}(r) = -(2 \sigma_N/hc) \hat{A}(r) \int_0^d e \tan(h \beta e) \text{Im}(f^2) \text{d} \mathbf{e}$, where $\sigma_N$ is the normal conductivity of the Al sample and $\beta = (k_B T)^{-1}$. The solution of the Maxwell equation yields the following expression for the depairing energy:

$$\Gamma = \frac{2D e^2}{h c^2} \langle \hat{A}^2 \rangle,$$

for the Green functions, we calculate the magnetic-field evolution of the Andreev spectra, reproducing the main experimental features without any additional parameter [see Fig. 3(c)]. The theoretical analysis of the critical field reveals that for $d > \lambda_0$, as in our case, both $\Delta$ and the spectral gap are finite up to the transition to the normal state. This naturally explains why this transition is of first order and why the zero-bias conductance is not modified by the field. The existence of this first-order transition in superconducting films was first discussed in the frame of the Ginzburg-Landau theory.21

In conclusion, we have presented a comprehensive experimental study of the transport through Al/Co nanocapacitors. We have also introduced a model for the description of the Andreev reflection in S/F interfaces. While retaining the simplicity of BTK-type theories, our model includes the effect of the spin-dependent transmission and allows the analysis of a great variety of realistic ingredients. We have shown that such a model consistently describes the whole set of measurements for arbitrary voltage, temperature, and magnetic field, which demonstrates that the current polarization in ferromagnets can be determined using Andreev physics. Moreover, our data and analysis provide important input for first-principles calculations of electron transmission through ferromagnetic interfaces.

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